National Semiconductor

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MM54HCT00/MM74HCT00 Quad 2 Input NAND Gate

General Description

The MM54HCT00/MM74HCT00 are NAND gates fabricated using advanced silicon-gate CMOS technology which provides the inherent benefits of CMOS—low quiescent power and wide power supply range. These devices are input and output characteristic and pin-out compatible with standard DM54LS/74LS logic families. All inputs are protected from static discharge damage by internal diodes to V_{CC} and ground.

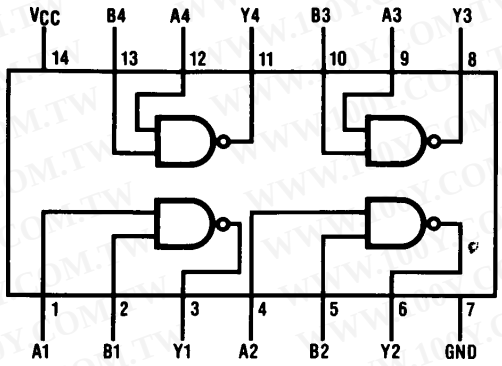
MM54HCT/MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

Features

- TTL, LS pin-out and threshold compatible
- Fast switching: t_{PLH}, t_{PHL} = 14 ns (typ)
- Low power: 10 μW at DC
- High fan out, 10 LS-TTL loads

Connection and Logic Diagrams

Dual-In-Line Package

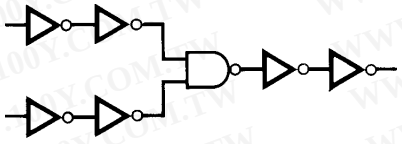


TL/F/5356–1

Top View

Order Number MM54HCT00 or MM74HCT00

(1 of 4 gates)



TL/F/5356–2

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	4.5	5.5	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HCT	−40	+85	°C
MM54HCT	−55	+125	°C
Input Rise or Fall Times (t_r, t_f)		500	ns

DC Electrical Characteristics V_{CC} = 5V ±10% (unless otherwise specified)

Symbol	Parameter	Conditions	T_A = 25°C	74HCT T_A = −40 to 85°C	54HCT T_A = −55 to 125°C	Units
			Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage			2.0	2.0	2.0	V
V_{IL}	Maximum Low Level Input Voltage			0.8	0.8	0.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IH} or V_{IL}					
		$\|I_{OUT}\|$ = 20 μA	V_{CC}	V_{CC} −0.1	V_{CC} −0.1	V_{CC} −0.1	V
		$\|I_{OUT}\|$ = 4.0 mA, V_{CC} = 4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\|$ = 4.8 mA, V_{CC} = 5.5V	5.2	4.98	4.84	4.7	V
V_{OL}	Maximum Low Level Voltage	V_{IN} = V_{IH}					
		$\|I_{OUT}\|$ = 20 μA	0	0.1	0.1	0.1	V
		$\|I_{OUT}\|$ = 4.0 mA, V_{CC} = 4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\|$ = 4.8 mA, V_{CC} = 5.5V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND, V_{IH} or V_{IL}		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND, I_{OUT} = 0 μA		2.0	20	40	μA
		V_{IN} = 2.4V or 0.5V (Note 4)	0.18	0.3	0.4	0.5	mA

AC Electrical Characteristics V_{CC} = 5.0V, t_r = t_f = 6 ns, C_L = 15 pF, T_A = 25°C (unless otherwise noted)

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PLH}, t_{PHL}	Maximum Propagation Delay		14	18	ns

AC Electrical Characteristics $V_{CC}=5.0V\pm10\%$, $t_r=t_f=6$ ns, $C_L=50$ pF (unless otherwise noted)

Symbol	Parameter	Conditions	$T_A=25°C$	74HCT $T_A=-40$ to $85°C$		54HCT $T_A=-55$ to $125°C$	Units
			Typ	Guaranteed Limits			
t_{PLH}, t_{PHL}	Maximum Propagation Delay		18	23	29	35	ns
t_{THL}, t_{TLH}	Maximum Output Rise & Fall Time		8	15	19	22	ns
C_{PD}	Power Dissipation Capacitance	(Note 5)	30				pF
C_{IN}	Input Capacitance		5	10	10	10	pF

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

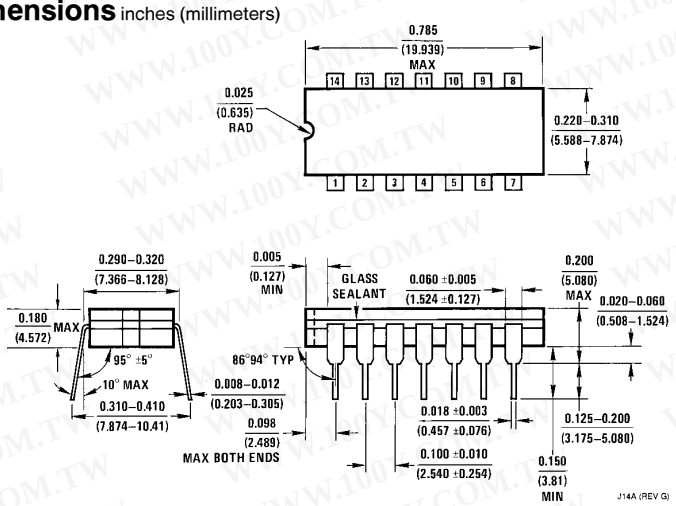
Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

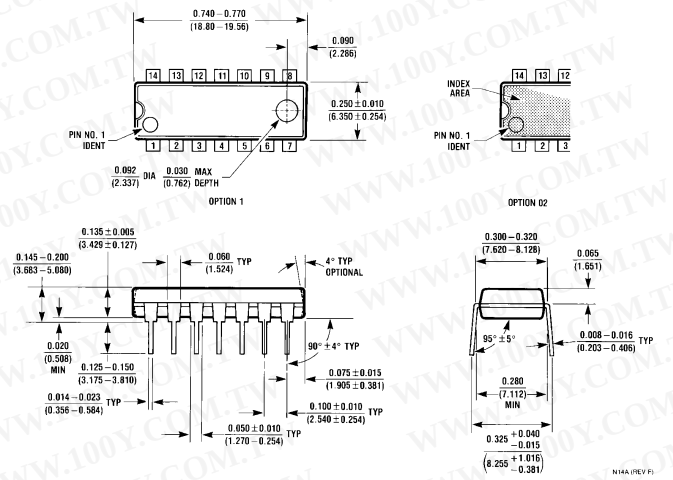
Note 4: This is measured per input with all other inputs held at V_{CC} or ground.

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD}\,V_{CC}^2\,f+I_{CC}\,V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD}\,V_{CC}\,f+I_{CC}$.

Physical Dimensions inches (millimeters)



Order Number MM54HCT00J or MM74HCT00J
NS Package J14A



Order Number MM74HCT00N
NS Package N14A

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.